

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)	Group Art Unit: 2811
)	
Osamu Goto, et al.)	Examiner: Ori Nadav
)	
Application No. 10/606,176)	Confirmation No.: 3458
)	
Filed: June 25, 2003)	
)	
For: SEMICONDUCTOR LIGHT EMITTING)	
DEVICE, ITS MANUFACTURING METHOD,)	
SEMICONDUCTOR DEVICE AND ITS)	
MANUFACTURING METHOD)	

MAIL STOP AMENDMENT
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Respectfully submitted,

Dated: August 25, 2006

By: _____



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Substitute for form 1449A/PTO			<div> <div>Complete if Known</div> <div> <div>Application Number</div> <div>10/606,176</div> </div> <div> <div>Filing Date</div> <div>June 25, 2003</div> </div> <div> <div>First Named Inventor</div> <div>Yoshihide Nakamura</div> </div> <div> <div>Art Unit</div> <div>2811</div> </div> <div> <div>Examiner Name</div> <div>Ori Nadav</div> </div> <div> <div>Attorney Docket Number</div> <div>09792909-5625</div> </div> </div>		
<div> <div>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</div> <div>(use as many sheets as necessary)</div> </div>					
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Examiner Signature		Date Considered	
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Substitute for form 1449B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Application Number	10/606,176
		Filing Date	June 25, 2003
		First Named Inventor	Yoshihide Nakamura
		Art Unit	2811
		Examiner Name	Ori Nadav
(use as many sheets as necessary)		Attorney Docket Number	09792909-5625
Sheet		of	

OTHER ITEMS – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
		<i>"InGaN Multi-Quantum-Well-Structure Laser Diodes with Cleaved Mirror Cavity Facets," Jpn. J. Appl. Phys., Vol. 35, 1996, pp. L217-L220</i>	
		<i>"Blue InGaN-Based Laser Diodes with an Emission Wavelength of 450nm" Appl. Phys. Lett., Vol. 76, 2000, pp. 22-24</i>	
		<i>"Fist III-V-Nitride-Based Violet Laser Diodes" J. Crystal Growth, Vol. 170, 1997, pp. 11-15</i>	
		<i>"High-Power, Long-Lifetime InGaN/GaN/AlGaIn-Based Laser Diodes Grown on Pure GaN Substrates." Jpn. J. Appl. Phys., Vol. 35, 1998, pp. L309-L312</i>	
		<i>"InGaN/GaN/AlGaIn-Based Laser Diodes Grown on Epitaxially Laterally Overgrown GaN," J. Mater. Res., Vol. 14, No. 7, 1999, pp. 2716-2731</i>	
		<i>"InGaN/GaN/AlGaIn-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices," Jpn. J. Appl. Phys., Vol. 36, 1997, pp. 1568-1571</i>	

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